



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

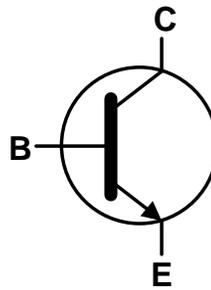
- $BV_{CE0} > 300V$
- $BV_{CBO} > 300V$
- $I_C = 0.5A$ High Continuous Current
- $I_{CM} = 1A$ Peak Pulse Current
- Complementary PNP Type: NK-FZT757

Mechanical Data

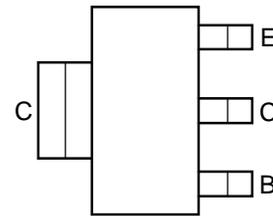
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	0.5	A
Peak Pulse Current	I _{CM}	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

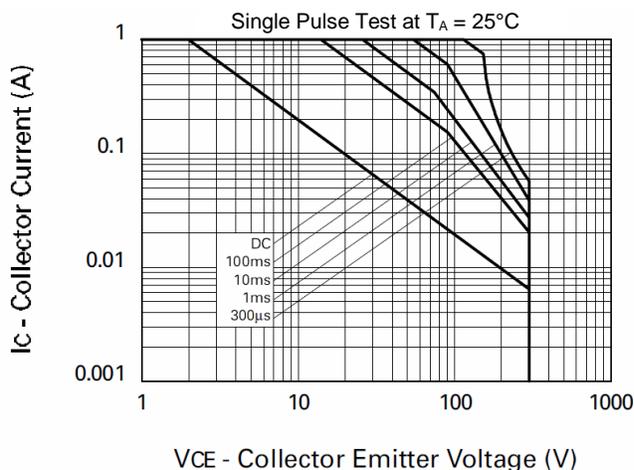
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 6)	3.0
		(Note 7)	2.0
		(Note 8)	1.6
		(Note 9)	1.2
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 6)	41.7
		(Note 7)	62.5
		(Note 8)	78.1
		(Note 9)	104
Thermal Resistance Junction to Lead	R _{θJL}	12.9	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 11)

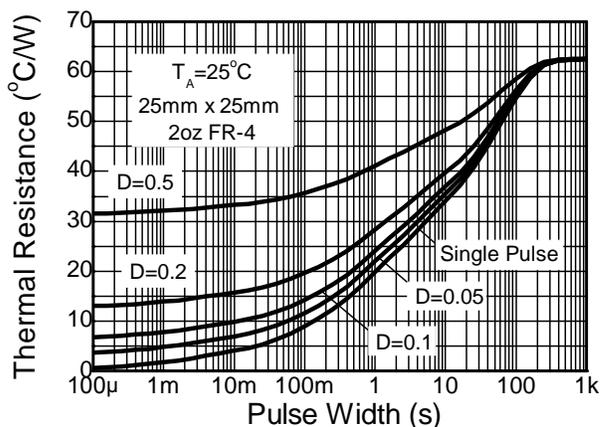
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
 8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
 9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
 10. Thermal resistance from junction to solder-point (at the end of the collector lead).
 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

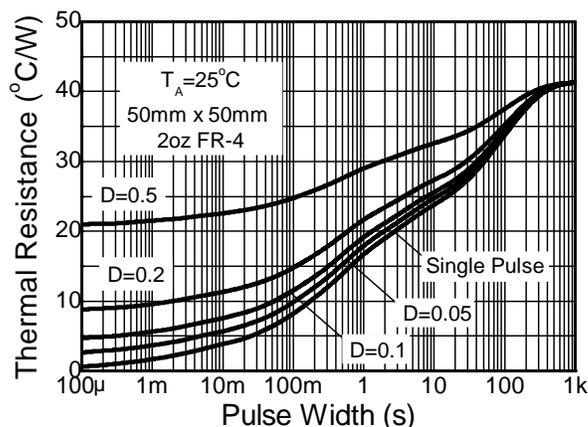
Thermal Characteristics and Derating Information



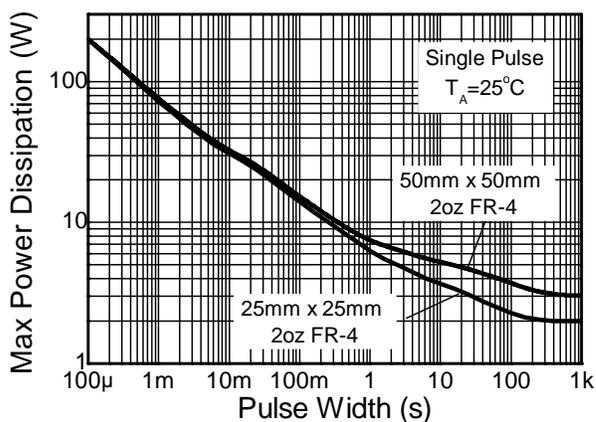
Safe Operating Area



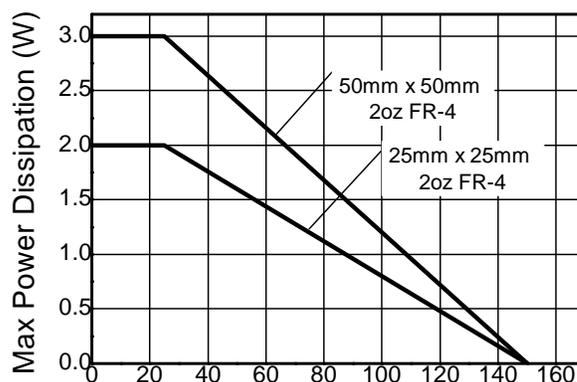
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



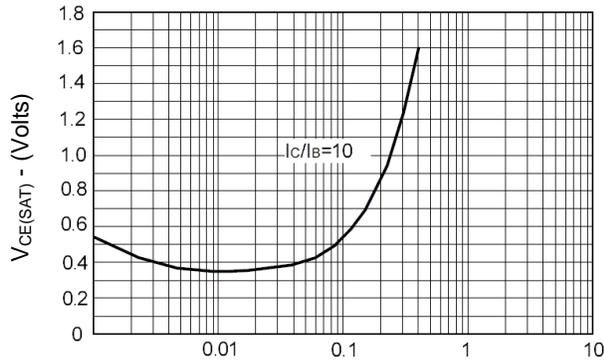
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	300	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	300	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	—	—	100	nA	V _{CB} = 200V
Emitter Cut-Off Current	I _{EBO}	—	—	100	nA	V _{EB} = 5.6V
DC Current Gain (Note 12)	h _{FE}	40 50	— —	— —	—	I _C = 10mA, V _{CE} = 5V I _C = 100mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(SAT)}	—	—	0.5	V	I _C = 100mA, I _B = 10mA
Base-Emitter Saturation Voltage (Note 12)	V _{BE(SAT)}	—	—	1.0	V	I _C = 100mA, I _B = 10mA
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(ON)}	—	—	1.0	V	I _C = 100mA, V _{CE} = 5V
Output Capacitance	C _{OBO}	—	—	20	pF	V _{CB} = 20V, f = 1MHz
Current Gain-Bandwidth Product	f _T	30	—	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 20MHz

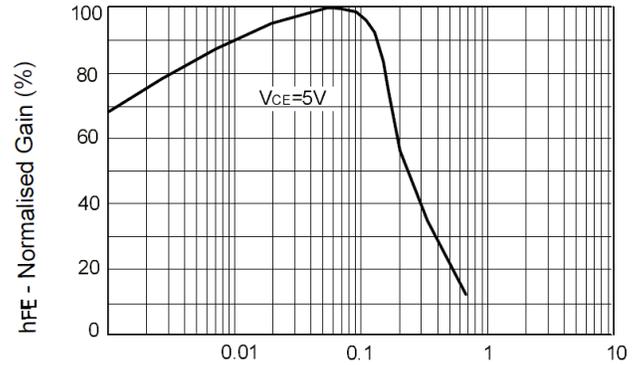
Note: 12. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



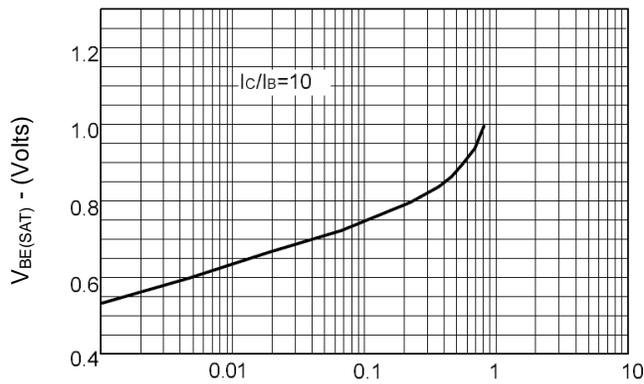
I_C - Collector Current (Amps)

$V_{CE(SAT)} \text{ v } I_C$



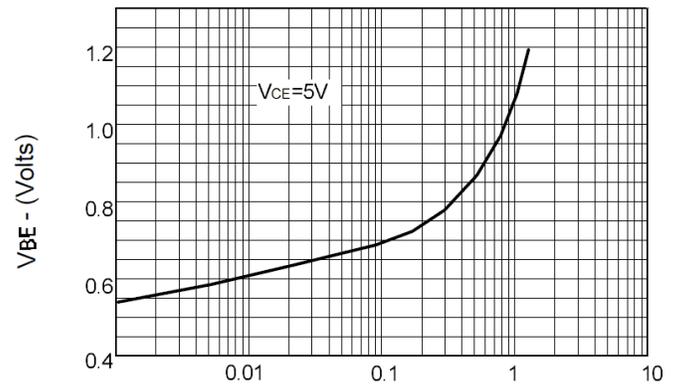
I_C - Collector Current (Amps)

$h_{FE} \text{ v } I_C$



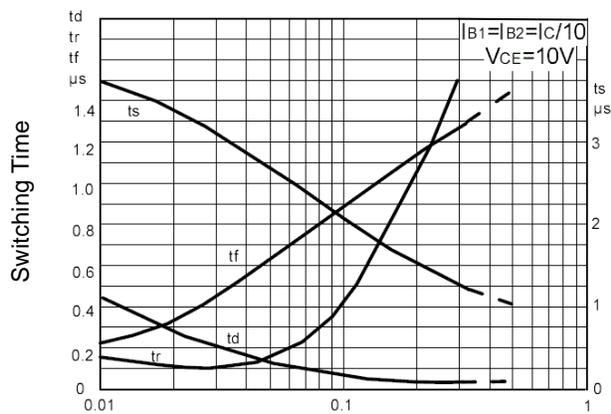
I_C - Collector Current (Amps)

$V_{BE(SAT)} \text{ v } I_C$



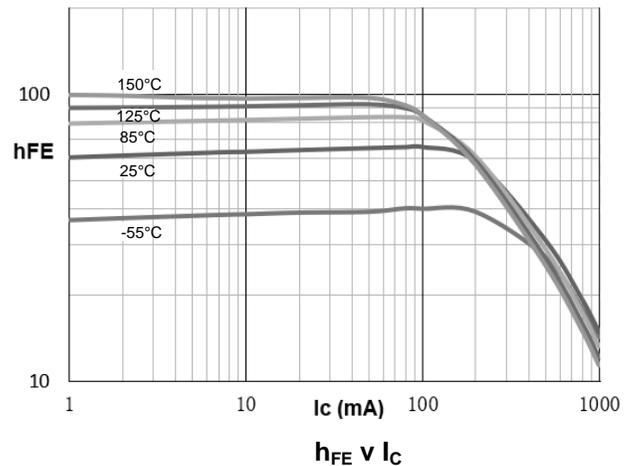
I_C - Collector Current (Amps)

$V_{BE(ON)} \text{ v } I_C$



I_C - Collector Current (Amps)

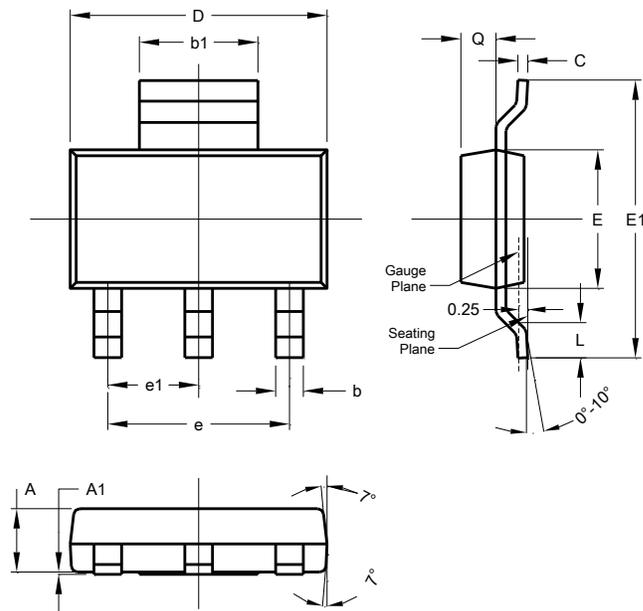
Switching Speeds



$h_{FE} \text{ v } I_C$

Package Outline Dimensions

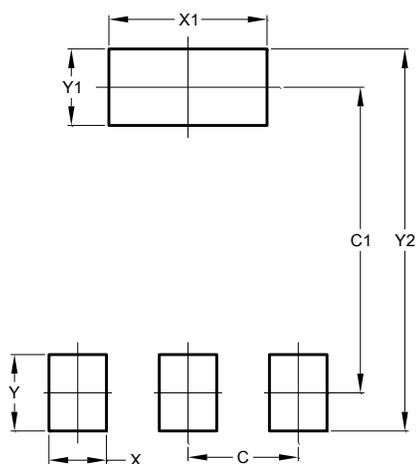
SOT223



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.